

S-8239B Series

Rev.1.1_04

OVERCURRENT MONITORING IC FOR MULTI-SERIAL-CELL PACK

www.ablicinc.com

© ABLIC Inc., 2014-2016

The S-8239B Series is an overcurrent monitoring IC for multi-serial-cell pack including high-accuracy voltage detection circuits and delay circuits.

The S-8239B Series is suitable for protection of lithium-ion / lithium polymer rechargeable battery packs from overcurrent.

Features

• Built-in high-accuracy voltage detection cir	cuit	
Overcurrent 1 detection voltage*1	0.04 V to 0.30 V (10 mV step)	Accuracy ±15 mV
Overcurrent 2 detection voltage	0.1 V to 0.7 V (100 mV step)	Accuracy ±100 mV
Overcurrent 3 detection voltage	1.2 V (Fixed)	Accuracy ±300 mV
• Built-in three-step overcurrent detection cir	cuit: Overcurrent 1, overcurrent 2, over	ercurrent 3
Overcurrent 3 detection function is selectal	ble: Available, unavailable	
 UVLO (under voltage lock out) function 		
UVLO detection voltage	2.0 V (Fixed)	Accuracy ±100 mV
 High-withstand voltage: 	VM pin, DO pin: Absolute maxim	um rating 28 V
• Delay times are generated only by an inter	nal circuit (External capacitors are un	necessary).
Low current consumption		
During normal operation:	7.0 μA max.	
During power-down:	0.1 μA max.	
Output logic:	Active "L"	
Wide operation temperature range:	Ta = -40° C to $+85^{\circ}$ C	
Lead-free (Sn 100%) halogen-free		

- Lead-free (Sn 100%), halogen-free
- *1. Overcurrent 1 detection voltage ≤ 0.06 V should be satisfied in the case of overcurrent 2 detection voltage = 0.1 V. Overcurrent 1 detection voltage ≤ 0.85 × overcurrent 2 detection voltage – 0.05 V should be satisfied in the case of overcurrent 2 detection voltage ≥ 0.2 V.

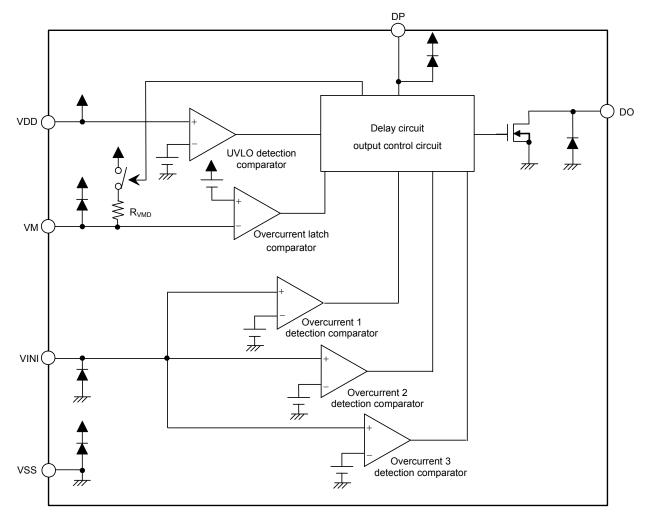
Applications

- Lithium-ion rechargeable battery pack
- Lithium polymer rechargeable battery pack

Package

• SOT-23-6

Block Diagram

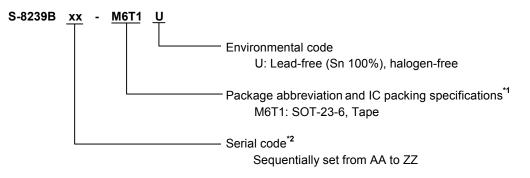


Remark All the diodes shown in the figure are parasitic diodes.

Figure 1

Product Name Structure

1. Product name



*1. Refer to the tape drawing.

*2. Refer to "3. Product name list".

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Таре	Reel
SOT-23-6	MP006-A-P-SD	MP006-A-C-SD	MP006-A-R-SD

3. Product name list

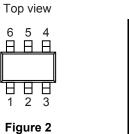
Table 2

Product Name	Overcurrent 1 Detection Voltage [V _{DIOV1}]	Overcurrent 2 Detection Voltage [V _{DIOV2}]	Overcurrent 1 Detection Delay Time [t _{DIOV1}]	Overcurrent 2 Detection Delay Time [t _{DIOV2}]	Overcurrent 3 Detection Function
S-8239BAA-M6T1U	0.20 V	0.4 V	1150 ms	0.56 ms	Unavailable

Remark Contact our sales office for the products with detection voltage value other than those specified above.

Pin Configuration

1. SOT-23-6



Pin No.	Symbol	Description
1	VINI	Voltage detection pin between VINI pin and VSS pin (Overcurrent detection pin)
2	VM	Overcurrent latch pin
3	DO	Connection pin of discharge control FET gate
4	DP ^{*1}	Test pin for delay time measurement
5	VDD	Input pin for positive power supply
6	VSS	Input pin for negative power supply

Table 3

*1. The DP pin should be open.

***1.** The DP pin should be open.

Absolute Maximum Ratings

Table 4

			(Ta = +25°C unless otherwise	specified)
Item	Symbol	Applied pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin	V _{DS}	VDD	$V_{\rm SS}-0.3$ to $V_{\rm SS}$ +12	V
VM pin input voltage	V _{VM}	VM	$V_{\text{DD}}-28$ to $V_{\text{DD}}+0.3$	V
VINI pin input voltage	V _{VINI}	VINI	$V_{\rm SS}-0.3$ to $V_{\rm SS}+12$	V
DO pin output voltage	V _{DO}	DO	$V_{\text{SS}}-0.3$ to $V_{\text{SS}}+28$	V
Power dissipation	PD	-	650 ^{*1}	mW
Operation ambient temperature	T _{opr}	-	-40 to +85	°C
Storage temperature	T _{stg}	_	–55 to +125	°C

*1. When mounted on board

[Mounted board]

(1) Board size: $114.3 \text{ mm} \times 76.2 \text{ mm} \times t1.6 \text{ mm}$

(2) Board name: JEDEC STANDARD51-7

Caution 1. The DP pin should be open.

2. The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

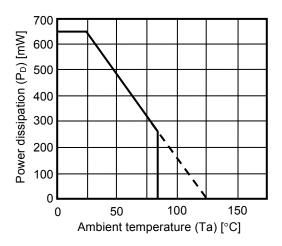


Figure 3 Power Dissipation of Package (When Mounted on Board)

Electrical Characteristics

1. Ta = +25°C

		Table 5		(Ta =	+25°C u	nless o	otherwise s	pecified
Item	Symbol	Condition	Min.	Тур.	Max.	Unit	Test Condition	Test
Detection Voltage								
Overcurrent 1 detection voltage	V _{DIOV1}	-	V _{DIOV1} - 0.015	V _{DIOV1}	V _{DIOV1} + 0.015	V	1	1
Overcurrent 2 detection voltage ^{*1}	V_{DIOV2}	-	V _{DIOV2} - 0.100	V _{DIOV2}	V _{DIOV2} + 0.100	V	1	1
Overcurrent 3 detection voltage	V _{DIOV3}	Overcurrent 3 detection function "available"	0.90	1.20	1.50	V	1	1
UVLO detection voltage	V_{UVLO}	_	1.90	2.00	2.10	V	1	1
Release Voltage								
Overcurrent release voltage	V _{RIOV}	V _{DD} criteria, V _{DD} = 3.5 V	0.7	1.2	1.5	V	1	1
Input Voltage, Operation Voltag	je							
Operation voltage between VDD pin and VSS pin	V _{DSOP}	Output logic is determined ^{*2}	1.5	-	8	V	-	-
Current Consumption								
Current consumption during normal operation	I _{OPE}	V _{DD} = 3.5 V, V _{VM} = 0 V	1.0	3.5	7.0	μA	2	2
Current consumption during power-down	I _{PDN}	V _{DD} = V _{VM} = 1.5 V	_	_	0.1	μA	2	2
Internal Resistance								
Internal resistance between VM pin and VDD pin	R _{VMD}	V _{DD} = 1.8 V, V _{VM} = 0 V	100	300	900	kΩ	3	3
Output Resistance								
DO pin resistance "L"	R _{DOL}	$V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V$	2.5	5	10	kΩ	4	4
Delay Time								
Overcurrent 1 detection delay time	t _{DIOV1}	_	t _{DIOV1} × 0.6	t _{DIOV1}	t _{DIOV1} × 1.4	ms	5	5
Overcurrent 2 detection delay time	t _{DIOV2}	-	$t_{DIOV2} \times 0.6$	t _{DIOV2}	$t_{DIOV2} \times 1.4$	ms	5	5
Overcurrent 3 detection delay time	t _{DIOV3}	Overcurrent 3 detection function "available"	168	280	392	μS	5	5
UVLO detection delay time	t _{UVLO}	-	2.94	4.90	6.86	s	5	5

*1. Even if overcurrent 1 detection voltage and overcurrent 2 detection voltage are in the same range, V_{DIOV1} is lower than V_{DIOV2}.

***2.** It indicates that DO pin output logic is determined.

OVERCURRENT MONITORING IC FOR MULTI-SERIAL-CELL PACK S-8239B Series

2. Ta = -40° C to $+85^{\circ}$ C^{*1}

Rev.1.1_04

ItemSymbolConditionMin.I yp.Max.UnitConditionCond			Table 6	(Ta = _4	0°C to ₌	-85°C ^{*1} ⊔	inless (otherwise s	necified
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Item	Symbol						Test	Test
Overcurrent 1 detection voltageV blov1- -0.021 V blov1 $+0.021$ V1Overcurrent 2 detection voltageV blov2-V blov2V blov2V blov2V blov2V blov2V blov3V1Overcurrent 3 detection voltageV blov3Overcurrent 3 detection function "available"0.701.201.70V1UVLO detection voltageV blov4-1.852.002.15V1Overcurrent release voltageV blov5V blov51.21.77V1Input Voltage, Operation VoltageV bosopOutput logic is determined"31.5-8V-Current ConsumptionV bosopOutput logic is determined"31.5-8VCurrent Consumption during normal operationIoPEV bosopOutput 1.5 V0.758.0 μA 2Internal ResistanceIPDNV bosopV bosop0.773.58.0 μA 22Internal ResistanceIPDNV bosopV bosop0.773.58.0 μA 2Internal ResistanceIPDNV bosopV bosop0.15 μA 2Internal ResistanceIPDNV bosopV bosop0.5 V Vosop0.15 μA 2Internal ResistanceIPDNV bosopV bosop0.5 V Vosop1.251.5 $k \Omega$ 4	Detection Voltage								
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Overcurrent 1 detection voltage	V _{DIOV1}	-	-0.021	V _{DIOV1}	+ 0.021	V	1	1
Overcurrent 3 detection voltageVDIOV3"available"0.701.201.70V1UVLO detection voltageVUVLO-1.852.002.15V1Release VoltageOvercurrent release voltageVRIOVVDD criteria, VDD = 3.5 V0.51.21.7V1Input Voltage, Operation VoltageOperation voltage between VDD pin and VSS pinVDD output logic is determined*31.5-8V-Current ConsumptionCurrent consumption during normal operationIoPEVDD = 3.5 V, VVM = 0 V0.73.58.0 μA 2Current consumption during power-downIPDNVDD = VVM = 1.5 V0.15 μA 2Internal ResistanceInternal ResistanceVDD = 1.8 V, VVM = 0 V783001310kΩ3Output ResistanceRVMDVDD = VVINI = 3.5 V, VDD = 0.5 V1.2515kΩ4DO pin resistance between VDD pinVDD = VVINI = 3.5 V, VDD = 0.5 V1.2515kΩ4Delay TimeOvercurrent 1 detection delay timetoiOV1-toiOV1toiOV1toiOV1toiOV2 x1.8ms5Overcurrent 2 detection delay timetoiOV2toiOV2 x1.8toiOV2 x1.8foiOV2 x1.855Overcurrent 3 detection delay timetoiOV3Overcurrent 3 detection fun	Overcurrent 2 detection voltage*2	V _{DIOV2}	-	V _{DIOV2} - 0.130	V_{DIOV2}		V	1	1
Release VoltageOvercurrent release voltage V_{RIOV} V_{DD} criteria, $V_{DD} = 3.5$ V 0.5 1.2 1.7 V 1 Input Voltage, Operation VoltageOperation voltage between VDD pin and VSS pin V_{DSOP} Output logic is determined*3 1.5 $ 8$ V $-$ Current Consumption ormal operation V_{DSOP} Output logic is determined*3 1.5 $ 8$ V $-$ Current consumption during power-down I_{OPE} $V_{DD} = 3.5$ V, $V_{VM} = 0$ V 0.7 3.5 8.0 μA 2 Current consumption during 	Overcurrent 3 detection voltage	V _{DIOV3}		0.70	1.20	1.70	V	1	1
Overcurrent release voltage V_{RIOV} V_{DD} criteria, V_{DD} = 3.5 V0.51.21.7V1Input Voltage, Operation VoltageOperation voltage between VDD pin and VSS pin V_{DSOP} Output logic is determined"31.5-8V-Current ConsumptionIOPE V_{DSOP} Output logic is determined"31.5-8V-Current Consumption during normal operationIOPE V_{DD} = 3.5 V, V_{VM} = 0 V0.73.58.0 μA 2Current consumption during power-downIPDN V_{DD} = V_{VM} = 1.5 V0.15 μA 2Internal ResistanceInternal resistance between VM pin and VDD pin V_{DD} = 1.8 V, V_{VM} = 0 V783001310 $k\Omega$ 3Output Resistance Do pin resistance "L" R_{DOL} V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V1.2515 $k\Omega$ 4Delay TimeOvercurrent 1 detection delay time t_{DIOV1} - t_{DIOV2} t_{DIO	UVLO detection voltage	V_{UVLO}	_	1.85	2.00	2.15	V	1	1
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Release Voltage								
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Overcurrent release voltage	V _{RIOV}	V _{DD} criteria, V _{DD} = 3.5 V	0.5	1.2	1.7	V	1	1
VDD pin and VSS pinVDSOPOutput logic is determined1.5-8V-Current ConsumptionIopeV_DD = 3.5 V, V_{VM} = 0 V0.73.58.0 μA 2Current consumption during power-downIopeV_DD = V_{VM} = 1.5 V0.15 μA 2Internal ResistanceInternal resistance between VM pin and VDD pin R_{VMD} $V_{DD} = 1.8 V, V_{VM} = 0 V$ 783001310k Ω 3Output ResistanceRV_DD = V_{VINI} = 3.5 V, V_{DD} = 0.5 V1.2515 $k\Omega$ 4Do pin resistance "L" R_{DOL} $V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V$ 1.2515 $k\Omega$ 4Delay TimeVolovitime T_{DIOV1} T_{DIOV1} T_{LIR} ms55Overcurrent 1 detection delay time t_{DIOV2} $ t_{DIOV2}$ t_{DIOV2} T_{LIR} ms5Overcurrent 3 detection delay time t_{DIOV3} 0 Overcurrent 3 detection function "available"56280504 μ s5	Input Voltage, Operation Voltag	je							
		V _{DSOP}	Output logic is determined*3	1.5	_	8	V	_	_
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Current Consumption								
$\begin{array}{c c c c c c c c c c c c c c c c c c c $, ÷	I _{OPE}	V_{DD} = 3.5 V, V_{VM} = 0 V	0.7	3.5	8.0	μA	2	2
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		I _{PDN}	V _{DD} = V _{VM} = 1.5 V	I	_	0.15	μA	2	2
VM pin and VDD pinR_{VMD}V_{DD} = 1.8 V, V_{VM} = 0 V783001310 $K\Omega$ 3Output ResistanceDO pin resistance "L"R_{DOL}V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V1.2515 $k\Omega$ 4Delay TimeOvercurrent 1 detection delay time t_{DIOV1} $ t_{DIOV1}$ t_{DIOV1} t_{DIOV1} $k\Omega$ 4Overcurrent 2 detection delay time t_{DIOV2} $ t_{DIOV2}$ t_{DIOV2} t_{DIOV2} ms 5Overcurrent 3 detection delay time t_{DIOV3} 0 0 0 0 56 280 504 μs 5	Internal Resistance								
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		R _{VMD}	V _{DD} =1.8 V, V _{VM} = 0 V	78	300	1310	kΩ	3	3
Delay TimeOvercurrent 1 detection delay time t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{NR} $S5$ Overcurrent 2 detection delay time t_{DIOV2} t_{DIOV2} $ t_{DIOV2}$ t_{DIOV2} t_{DIOV2} ms 55 Overcurrent 3 detection delay time t_{DIOV3} t_{DIOV3} Overcurrent 3 detection function "available" 56 280 504 μs 55	Output Resistance								
Overcurrent 1 detection delay time t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} t_{DIOV1} x 1.8ms5Overcurrent 2 detection delay time t_{DIOV2} t_{DIOV2} $ t_{DIOV2}$ t_{DIOV2} t_{DIOV2} x 1.8ms5Overcurrent 3 detection delay time t_{DIOV3} 0 <td>DO pin resistance "L"</td> <td>R_{DOL}</td> <td>$V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V$</td> <td>1.2</td> <td>5</td> <td>15</td> <td>kΩ</td> <td>4</td> <td>4</td>	DO pin resistance "L"	R _{DOL}	$V_{DD} = V_{VINI} = 3.5 V, V_{DO} = 0.5 V$	1.2	5	15	kΩ	4	4
time t_{DIOV1} $ \times 0.2$ t_{DIOV1} $\times 1.8$ ms5Overcurrent 2 detection delay time t_{DIOV2} $ t_{DIOV2}$ $\times 0.2$ t_{DIOV2} $\times 0.2$ t_{DIOV2} $\times 1.8$ ms5Overcurrent 3 detection delay time t_{DIOV3} Overcurrent 3 detection function "available"56280504 μ s55	Delay Time								
time t_{DIOV2} $ \times 0.2$ t_{DIOV2} $\times 1.8$ ms5Overcurrent 3 detection delay time t_{DIOV3} t_{DIOV3} Overcurrent 3 detection function "available"56280504 μ s5	•	t _{DIOV1}	_		t _{DIOV1}		ms	5	5
Overcurrent 3 detection delay t _{DIOV3} Overcurrent 3 detection function 56 280 504 µs 5		t _{DIOV2}	-		t _{DIOV2}		ms	5	5
		t _{DIOV3}		56	280	504	μS	5	5
$ UVLO $ detection delay time $ t_{UVLO} $ – $ 0.98 4.90 8.82 s 5 $	UVLO detection delay time	t _{UVLO}	_	0.98	4.90	8.82	S	5	5

*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

*2. Even if overcurrent 1 detection voltage and overcurrent 2 detection voltage are in the same range, V_{DIOV1} is lower than V_{DIOV2}.

***3.** It indicates that DO pin output logic is determined.

Test Circuits

- Caution Unless otherwise specified, the output voltage levels "H" and "L" at the DO pin (V_{DO}) are judged by the threshold voltage (1.0 V) of the N-channel FET. Judge the DO pin level with respect to V_{ss}.
- Overcurrent 1 detection voltage, overcurrent 2 detection voltage, overcurrent release voltage, UVLO detection voltage (Test condition 1, test circuit 1)

The overcurrent 1 detection voltage (V_{DIOV1}) is defined as the voltage V2 whose delay time for changing V_{DO} from "H" to "L" lies between the minimum and the maximum value of the overcurrent 1 detection delay time after the voltage V2 is increased instantaneously (within 10 μ s) from the set conditions of V1 = V3 = 3.5 V, V2 = 0 V.

The overcurrent 2 detection voltage (V_{DIOV2}) is defined as the voltage V2 whose delay time for changing V_{DO} from "H" to "L" lies between the minimum and the maximum value of the overcurrent 2 detection delay time after the voltage V2 is increased instantaneously (within 10 µs) from the set conditions of V1 = V3 = 3.5 V, V2 = 0 V.

The overcurrent release voltage (V_{RIOV}) is defined as the voltage V3 at which V_{DO} goes from "L" to "H" after decreasing V2 to 0 V and the voltage V3 is increased gradually from the set conditions of V1 = V2 = 3.5 V, V3 = 0 V.

The UVLO detection voltage (V_{UVLO}) is defined as the voltage V1 at which V_{DO} goes from "H" to "L" after the voltages V1 and V3 are decreased gradually from the set conditions of V1 = V3 = 3.5 V, V2 = 0 V.

2. Overcurrent 3 detection voltage (Overcurrent 3 detection function "available") (Test condition 1, test circuit 1)

The overcurrent 3 detection voltage (V_{DIOV3}) is defined as the voltage V2 whose delay time for changing V_{DO} from "H" to "L" lies between the minimum and the maximum value of the overcurrent 3 detection delay time after the voltage V2 is increased instantaneously (within 10 µs) from the set conditions of V1 = V3 = 3.5 V, V2 = 0 V.

3. Current consumption during normal operation, current consumption during power-down (Test condition 2, test circuit 2)

The current consumption during normal operation (I_{OPE}) is the current that flows through the VDD pin (I_{DD}) under the set conditions of V1 = 3.5 V, V2 = 0 V.

The current consumption during power-down (I_{PDN}) is I_{DD} under the set conditions of V1 = V2 = 1.5 V.

4. Internal resistance between VM pin and VDD pin (Test condition 3, test circuit 3)

The internal resistance between the VM pin and the VDD pin (R_{VMD}) is the resistance between the VM pin and the VDD pin under the set conditions of V1 = 1.8 V, V2 = V3 = 0 V.

5. DO pin resistance "L" (Test condition 4, test circuit 4)

The DO pin resistance "L" (R_{DOL}) is the DO pin resistance under the set conditions of V1 = V2 = 3.5 V, V3 = 0.5 V.

6. Overcurrent 1 detection delay time (Test condition 5, test circuit 5)

6. 1 V_{DIOV2} = 0.1 V

The overcurrent 1 detection delay time (t_{DIOV1}) is the time period from when the voltage V2 exceeds V_{DIOV1} to when V_{DO} goes to "L", after V2 is increased to 0.08 V instantaneously (within 10 µs) under the set conditions of V1 = 3.5 V, V2 = 0 V.

6. 2 $V_{\text{DIOV2}} \ge 0.2 \text{ V}$

The overcurrent 1 detection delay time (t_{DIOV1}) is the time period from when the voltage V2 exceeds V_{DIOV1} to when V_{DO} goes to "L", after V2 is increased to V_{DIOV1} max. + 0.01 V instantaneously (within 10 µs) under the set conditions of V1 = 3.5 V, V2 = 0 V.

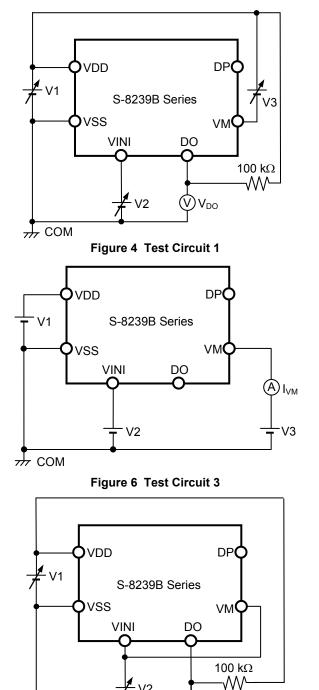
7. Overcurrent 2 detection delay time, UVLO detection delay time (Test condition 5, test circuit 5)

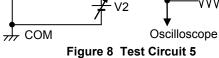
The overcurrent 2 detection delay time (t_{DIOV2}) is the time period from when the voltage V2 exceeds V_{DIOV2} to when V_{DO} goes to "L", after V2 is increased to 0.9 V instantaneously (within 10 µs) under the set conditions of V1 = 3.5 V, V2 = 0 V.

The UVLO detection delay time (t_{UVLO}) is the time period from when the voltage V1 falls below V_{UVLO} to when V_{DO} goes to "L", after V1 is decreased to 1.8 V instantaneously (within 10 µs) under the set conditions of V1 = 3.5 V, V2 = 0 V.

8. Overcurrent 3 detection delay time (Overcurrent 3 detection function "available") (Test condition 5, test circuit 5)

The overcurrent 3 detection delay time (t_{DIOV3}) is the time period from when the voltage V2 exceeds V_{DIOV3} to when V_{DO} goes to "L", after V2 is increased to 1.6 V instantaneously (within 10 µs) under the set conditions of V1 = 3.5 V, V2 = 0 V.





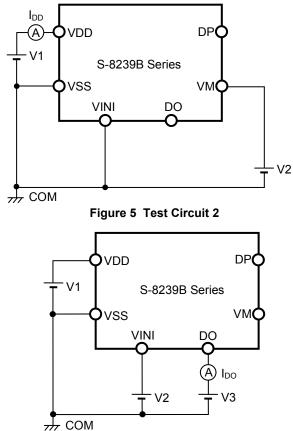


Figure 7 Test Circuit 4

Operation

1. Normal status

The S-8239B Series monitors the voltage between the VINI pin and the VSS pin to control discharging. When the VINI pin voltage is equal to or lower than the overcurrent 1 detection voltage (V_{DIOV1}), the DO pin becomes "High-Z". This status is called the normal status.

Caution When a battery is connected for the first time, the S-8239B Series may not be in the normal status. In this case, short the VM pin and VSS pin or connect the charger. The S-8239B Series then becomes the normal status.

2. Overcurrent status (Overcurrent 1, overcurrent 2, overcurrent 3)

When a battery is in the normal status, if the VINI pin voltage is equal to or higher than the overcurrent detection voltage because the discharge current is equal to or higher than the specified value and the status continues for the overcurrent detection delay time or longer, the DO pin becomes V_{SS} potential. This status is called the overcurrent status. The overcurrent status is retained when the voltage between the VDD pin and the VM pin is equal to or lower than the overcurrent release voltage (V_{RIOV}).

In the overcurrent status, the VM pin and the VDD pin are shorted by the internal resistance between the VM pin and the VDD pin (R_{VMD}) in the S-8239B Series.

After that, the overcurrent status is released if the voltage between the VDD pin and the VM pin becomes equal to or higher than V_{RIOV} by connecting a charger.

3. UVLO status

The S-8239B Series includes a UVLO (under voltage lock out) function to prevent the IC malfunction due to the decrease of the battery voltage when detecting the overcurrent. When the battery voltage in the normal status is equal to or lower than the UVLO detection voltage (V_{UVLO}) and the status continues for the UVLO detection delay time (t_{UVLO}) or longer, the DO pin becomes V_{SS} potential. This status is called the UVLO status.

In the UVLO status, the VM pin and the VDD pin are shorted by R_{VMD} between the VM pin and the VDD pin in the S-8239B Series.

After that, the UVLO status is released if the battery voltage becomes equal to or higher than V_{UVLO}.

4. Power-down status

In the UVLO status, the current consumption is decreased to the current consumption during power-down (I_{PDN}) if the voltage between the VDD pin and the VM pin becomes equal to or lower than 0.7 V typ. in the S-8239B Series. This status is called the power-down status.

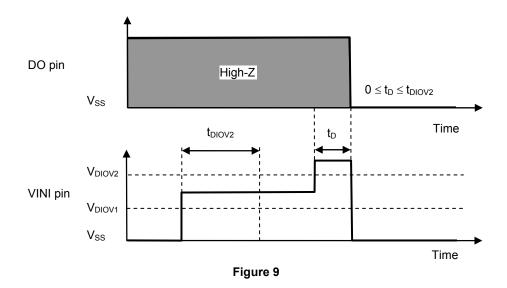
Moreover, if the voltage between the VDD pin and the VM pin becomes equal to or lower than 0.7 V typ. and the status continues for t_{UVLO} or longer in the normal status, the DO pin becomes V_{SS} potential and the S-8239B Series becomes power-down status.

After that, the power-down status is released if the voltage between the VDD pin and the VM pin is equal to or higher than 0.7 V typ. by connecting a charger.

5. Delay circuit

The detection delay times are determined by dividing a clock of approximately 3.5 kHz with the counter.

Remark The overcurrent 2 detection delay time (t_{DIOV2}) starts when the overcurrent 1 detection voltage (V_{DIOV1}) is detected. When the overcurrent 2 detection voltage (V_{DIOV2}) is detected over t_{DIOV2} after the detection of V_{DIOV1} , the S-8239B Series becomes the overcurrent status within t_{DIOV2} from the time of detecting V_{DIOV2} .



6. DP pin

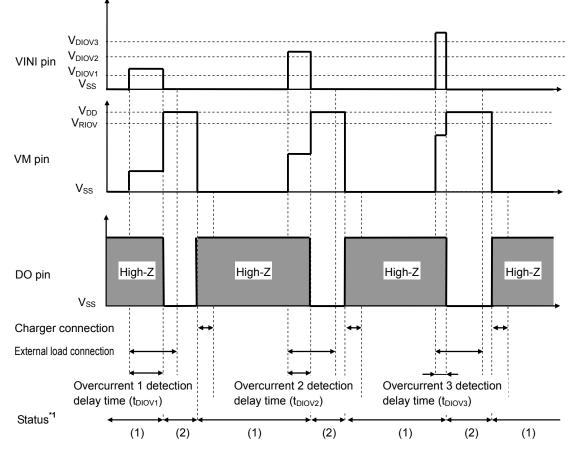
The DP pin is a test pin for delay time measurement and it should be open in the actual application. If a capacitor whose capacitance is 1000 pF or more or a resistor whose resistance is 1 M Ω or less is connected to this pin, error may occur in the delay times or in the detection voltages.

■ Timing Charts

Rev.1.1_04

1. Overcurrent detection

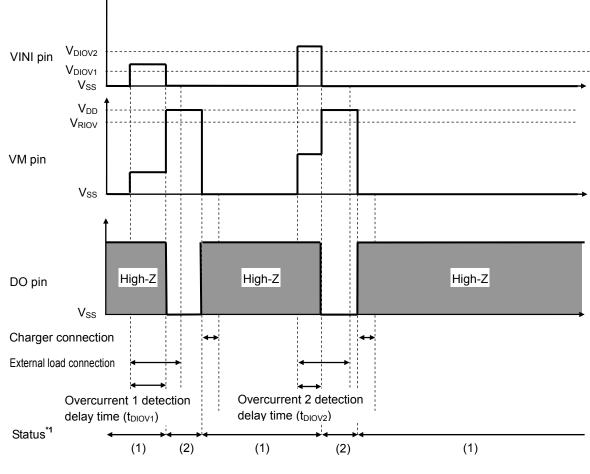
1.1 Overcurrent 3 detection function "available"



*1. (1): Normal status

(2): Overcurrent status

Figure 10



1.2 Overcurrent 3 detection function "unavailable"

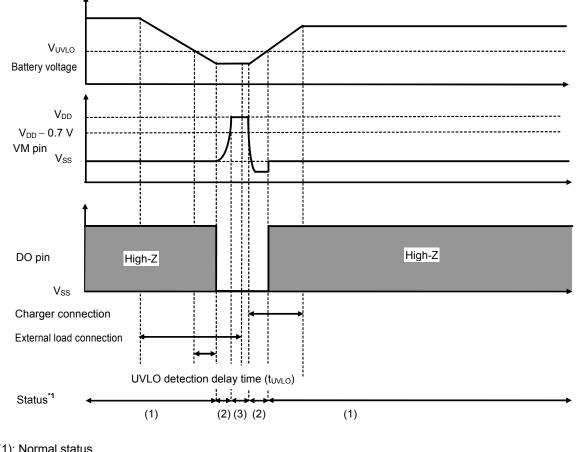
*1. (1): Normal status

(2): Overcurrent status

Figure 11

2. UVLO detecion

Rev.1.1_04



*1. (1): Normal status

(2): UVLO status

(3): Power-down status

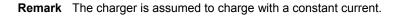


Figure 12

■ 5-serial-cell Protection Circuit Example

Figure 13 shows the 5-serial-cell protection circuit example used by the S-8239B Series and the S-8225A Series. Contact our sales office when using the circuit other than the following protection circuit example.

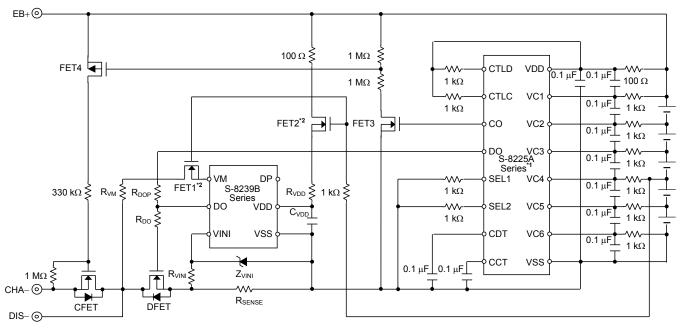


Figure 13

Table 7 Constants f	for External Components
---------------------	-------------------------

Symbol	Min.	Тур.	Max.	Unit
R _{VDD}	300	470	1000	Ω
R _{VINI}	1	-		kΩ
R _{SENSE}	0	-		mΩ
R _{VM}	1	5.1	51	kΩ
R _{DO} *3	_	5.1		kΩ
R _{DOP}	330	510	2000	kΩ
C _{VDD}	0.022	0.1	1	μF

*1. Refer to the data sheet of the S-8225A Series for the recommended value for external components of the S-8225A Series.

- ***2.** Use the products with the same model number for FET1 and FET2.
- *3. Set up the optimal constant according to the FET in use.

Caution 1. The above constants may be changed without notice.

- 2. The example of connection shown above and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constant.
- 3. The DP pin should be open.

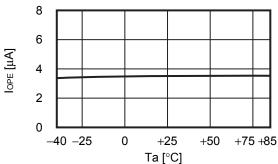
Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

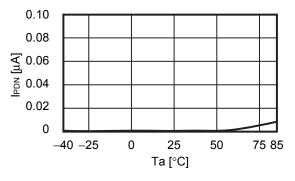
Characteristics (Typical Data)

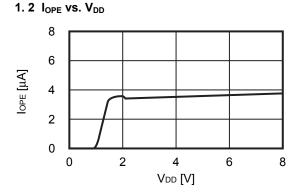
1. Current consumption





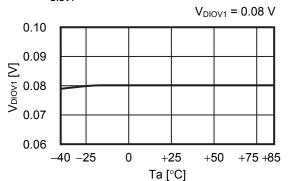


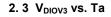


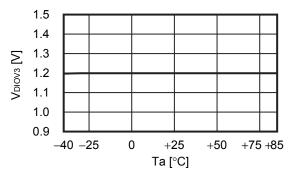


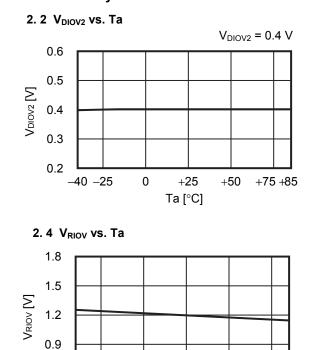
2. Overcurrent detection / release voltage, UVLO function and delay times

2.1 V_{DIOV1} vs. Ta









+25

Ta [°C]

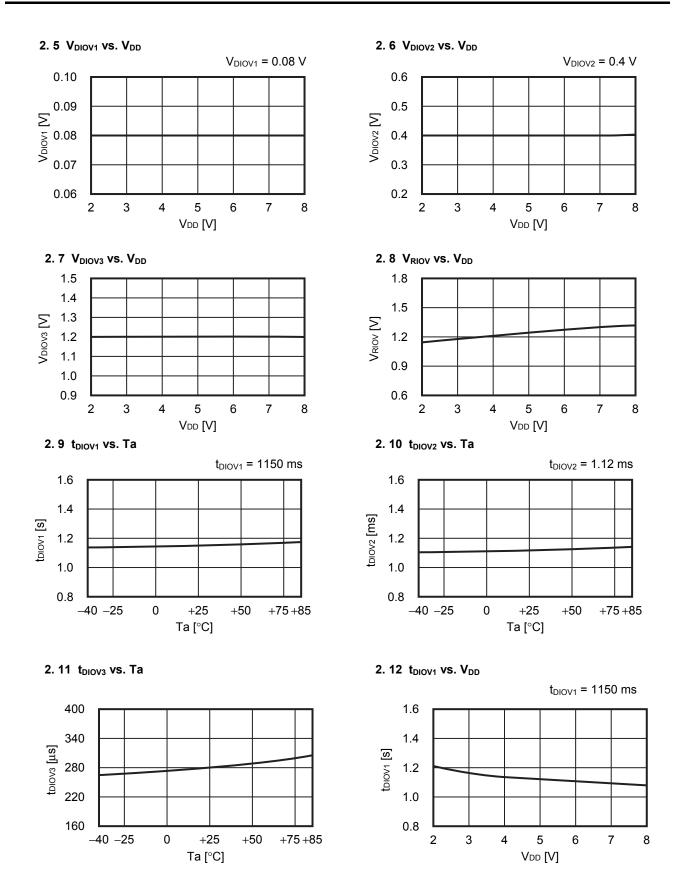
+50

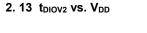
+75+85

0

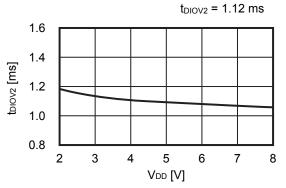
0.6

-40 -25

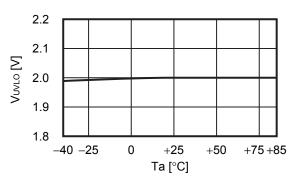




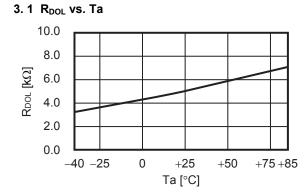
2. 14 t_{DIOV3} vs. V_{DD}

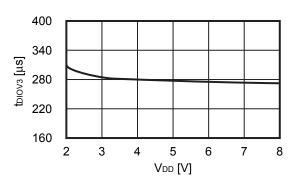


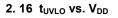


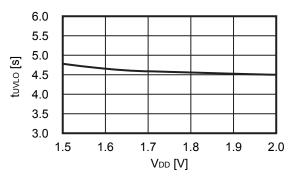


3. Output Resistance



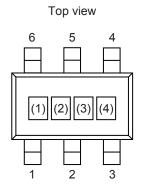






Marking Specification

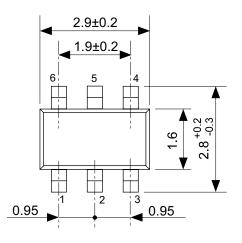
1. SOT-23-6

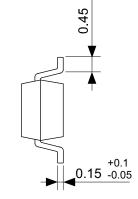


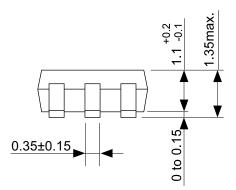
(1) to (3): (4): Product code (Refer to **Product name vs. Product code**) Lot number

Product name vs. Product code

Product Name	Pro	oduct Co	de
Product Name	(1)	(2)	(3)
S-8239BAA-M6T1U	3	L	А

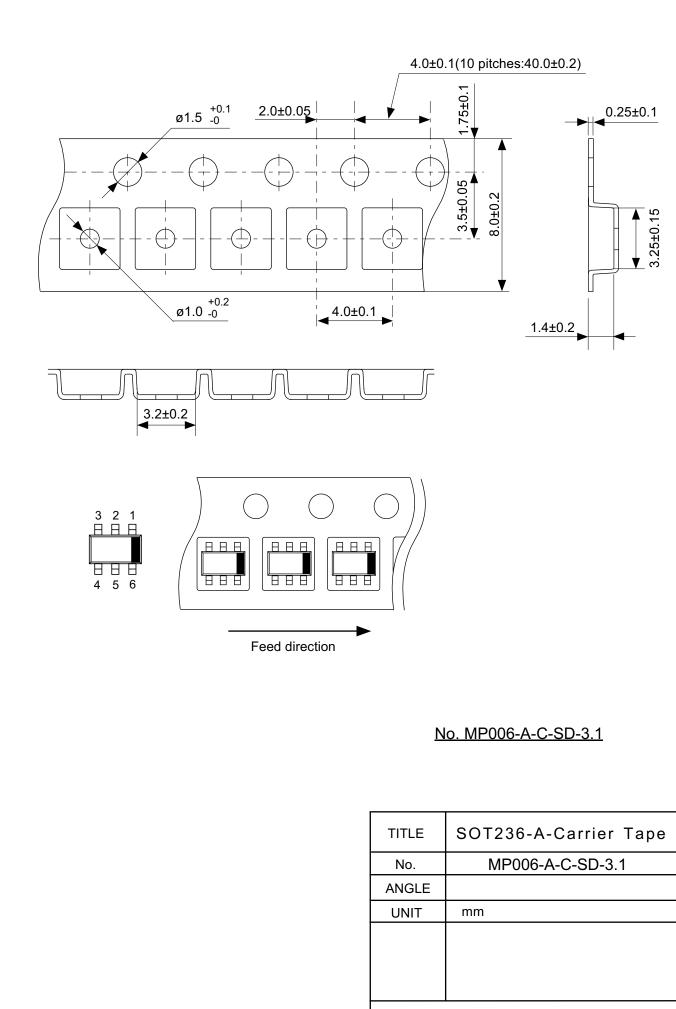




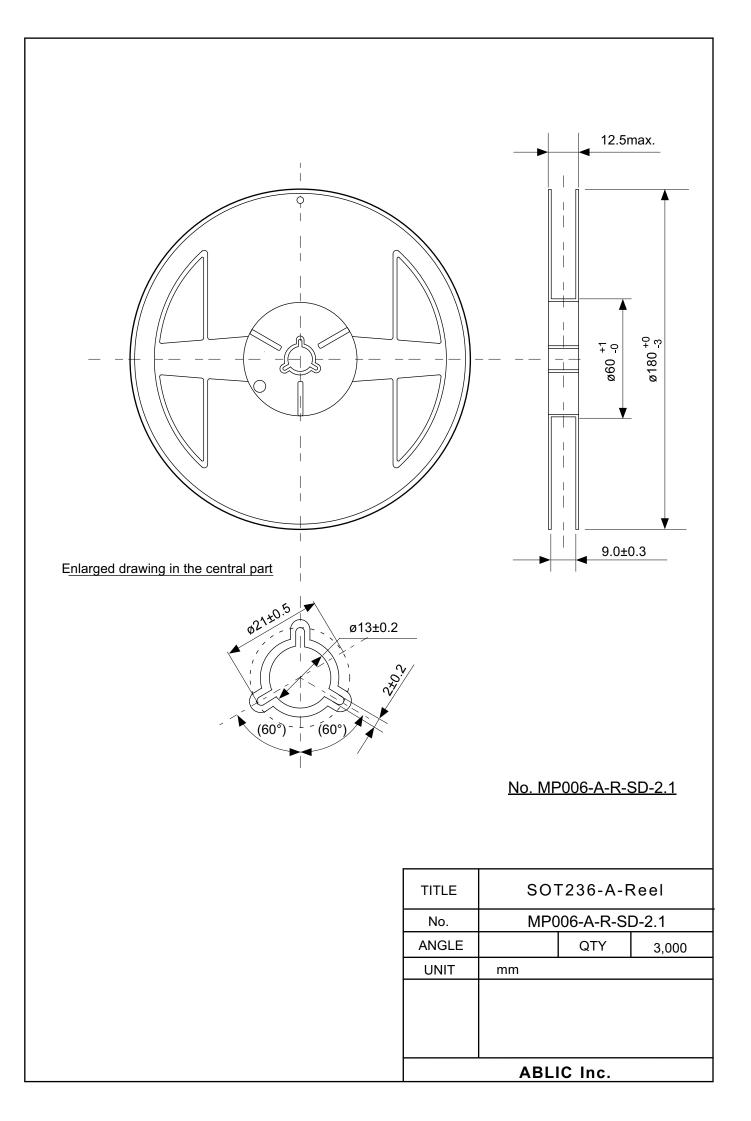


No. MP006-A-P-SD-2.1

TITLE	SOT236-A-PKG Dimensions		
No.	MP006-A-P-SD-2.1		
ANGLE	\oplus		
UNIT	mm		
	ABLIC Inc.		



ABLIC Inc.



Disclaimers (Handling Precautions)

- 1. All the information described herein (product data, specifications, figures, tables, programs, algorithms and application circuit examples, etc.) is current as of publishing date of this document and is subject to change without notice.
- The circuit examples and the usages described herein are for reference only, and do not guarantee the success of any specific mass-production design.
 ABLIC Inc. is not responsible for damages caused by the reasons other than the products described herein

ABLIC Inc. is not responsible for damages caused by the reasons other than the products described herein (hereinafter "the products") or infringement of third-party intellectual property right and any other right due to the use of the information described herein.

- 3. ABLIC Inc. is not responsible for damages caused by the incorrect information described herein.
- Be careful to use the products within their specified ranges. Pay special attention to the absolute maximum ratings, operation voltage range and electrical characteristics, etc.
 ABLIC Inc. is not responsible for damages caused by failures and / or accidents, etc. that occur due to the use of the products outside their specified ranges.
- 5. When using the products, confirm their applications, and the laws and regulations of the region or country where they are used and verify suitability, safety and other factors for the intended use.
- 6. When exporting the products, comply with the Foreign Exchange and Foreign Trade Act and all other export-related laws, and follow the required procedures.
- 7. The products must not be used or provided (exported) for the purposes of the development of weapons of mass destruction or military use. ABLIC Inc. is not responsible for any provision (export) to those whose purpose is to develop, manufacture, use or store nuclear, biological or chemical weapons, missiles, or other military use.
- 8. The products are not designed to be used as part of any device or equipment that may affect the human body, human life, or assets (such as medical equipment, disaster prevention systems, security systems, combustion control systems, infrastructure control systems, vehicle equipment, traffic systems, in-vehicle equipment, aviation equipment, aerospace equipment, and nuclear-related equipment), excluding when specified for in-vehicle use or other uses. Do not apply the products to the above listed devices and equipments without prior written permission by ABLIC Inc. Especially, the products cannot be used for life support devices, devices implanted in the human body and devices that directly affect human life, etc.

Prior consultation with our sales office is required when considering the above uses.

ABLIC Inc. is not responsible for damages caused by unauthorized or unspecified use of our products.

9. Semiconductor products may fail or malfunction with some probability. The user of the products should therefore take responsibility to give thorough consideration to safety design including redundancy, fire spread prevention measures, and malfunction prevention to prevent accidents causing injury or death, fires and social damage, etc. that may ensue from the products' failure or malfunction. The entire system must be sufficiently evaluated and applied on customer's own responsibility.

- 10. The products are not designed to be radiation-proof. The necessary radiation measures should be taken in the product design by the customer depending on the intended use.
- 11. The products do not affect human health under normal use. However, they contain chemical substances and heavy metals and should therefore not be put in the mouth. The fracture surfaces of wafers and chips may be sharp. Be careful when handling these with the bare hands to prevent injuries, etc.
- 12. When disposing of the products, comply with the laws and ordinances of the country or region where they are used.
- 13. The information described herein contains copyright information and know-how of ABLIC Inc. The information described herein does not convey any license under any intellectual property rights or any other rights belonging to ABLIC Inc. or a third party. Reproduction or copying of the information from this document or any part of this document described herein for the purpose of disclosing it to a third-party without the express permission of ABLIC Inc. is strictly prohibited.
- 14. For more details on the information described herein, contact our sales office.

2.0-2018.01

